

Please amend the paragraph beginning at page 3, line 14, as shown in the marked-up copy, to read as follows:

B²
The present invention may provide an electrode contact section of a sufficiently low contact resistance even when forming an impurity layer by ion implantation. The invention may provide an electrode contact section in which the contact resistance and the carrier injection coefficient can simultaneously be reduced.

Please amend the paragraph beginning at page 7, line 1, as shown in the marked-up copy, to read as follows:

B³
As shown, a p-type impurity layer 2 is formed in an n-type semiconductor substrate 1. The n-type semiconductor layer 1 contains an n-type impurity such as phosphorous (P) with a substantially constant concentration of approx. 10^{14} ions/cm³. The p-type impurity layer 2 is formed in a surface area of the semiconductor substrate 1 and contains a p-type impurity such as boron (B). The depth of the p-type impurity layer 2 from the surface of the semiconductor substrate 1 is set at 1.0 μ m or less, for example, approx. 0.8 μ m. Further, the peak value of the concentration profile of the p-type impurity layer 2 is set at a value falling within the range of 10^{17} - 10^{18} ions/cm³.

Please amend the paragraph beginning at page 13, line 20, as shown in the marked-up copy, to read as follows:

B⁴
In this example, a p-type impurity layer 2 is formed in an n-type semiconductor substrate 1. The n-type semiconductor layer 1 contains an n-type impurity such as phosphorus (P) with a substantially constant concentration of approx. 10^{14} ions/cm³. The p-type impurity layer 2 is formed in a surface area of the semiconductor substrate 1 and contains a p-type impurity such as boron (B). The depth of the p-type impurity layer 2 from the surface of the semiconductor substrate 1 is set at 1.0 μ m or less, for example, approx. 0.8 μ m. Further, the

B4
(cont'd)

peak value of the concentration profile of the p-type impurity layer 2 is set at a value falling within the range of 10^{17} - 10^{18} ions/cm³.

Please amend the paragraph beginning at page 52, line 4, as shown in the marked-up copy, to read as follows:

B5

Subsequently, an n-type impurity such as phosphorus (P) is implanted into the other surface of the semiconductor substrate 1 by ion implantation, and subjected to a thermal diffusion treatment, thereby forming an n⁺-type base layer 12 in a surface portion of the other surface of the semiconductor substrate 1.

Please amend the paragraph beginning at page 59, line 1, as shown in the marked-up copy, to read as follows:

B6

Subsequently, an n-type impurity such as phosphorus (P) is implanted into the other surface of the semiconductor substrate 1 by ion implantation, and subjected to a thermal diffusion treatment, thereby forming an n⁺-type base layer 12 in a surface portion of the other surface of the semiconductor substrate 1.

IN THE CLAIMS

Please amend the claims, as shown in the marked-up copy, to read as follows:

- B7
1. (Twice Amended) An electrode contact section incorporated in a semiconductor device, comprising:
- a first-conductivity-type semiconductor substrate;
 - a second-conductivity-type impurity layer formed in one surface of the semiconductor substrate and having a thickness of not more than $1.0\text{ }\mu\text{m}$ from the one surface of the semiconductor substrate;
 - a second-conductivity-type contact layer formed in the impurity layer and having a thickness of not more than $0.2\text{ }\mu\text{m}$ from the one surface of the semiconductor substrate, the